



JPW

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of:

Soo-doo CHAE, et al.

Art Unit: 2818

Serial No. 10/681,346

Examiner: Dung Anh Le

Filed: October 9, 2003

Confirmation No. 8321

For: METHOD FOR MANUFACTURING A SINGLE  
ELECTRON MEMORY DEVICE HAVING  
QUANTUM DOTS BETWEEN A GATE  
ELECTRODE AND A SINGLE ELECTRON  
STORAGE ELEMENT (As Amended)

Attorney Docket No. 249/286 DIV

**AMENDMENT UNDER 37 C.F.R. § 1.111 AFTER CLOSE OF PROSECUTION  
ON THE MERITS UNDER *EX PARTE QUAYLE***

Mail Stop Amendment  
Commissioner for Patents  
United States Patent and Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**INTRODUCTORY COMMENTS**

In response to the Office action mailed July 1, 2004, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Remarks** begin on page 3 of this paper.

**A replacement Abstract of the Disclosure** is attached at page 5 of this paper.